

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicants: Robert B. Ogle et al. 8/2
T. Step to
11-5022
Assignee: Advanced Micro Devices
Title: Oxidizing Pretreatment Of ONO Layer For Flash Memory (as amended)
Application No.: 10/010,280 Filing Date: December 5, 2001
Examiner: M. Pizarro-Crespo Group Art Unit: 2814
Docket No.: M-7522 US

San Jose, California
October 25, 2002

COMMISSIONER FOR PATENTS
Washington, D. C. 20231

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AMENDMENT

Dear Sir:

Applicants submit this amendment in response to the Office Action in this case having a mailing date of August 26, 2002.

IN THE TITLE

Please delete the current title and substitute the new title as follows:

--Oxidizing Pretreatment Of NON Layer For Flash Memory--

10/29/2002 NMOHAMM1 00000131 192386 10010280

01 FC:1202 18.00 CH
02 FC:1201 40.00 CH

IN THE CLAIMS

Please amend Claims 1-14 as follows: (An Appendix is attached hereto showing the changes to the claims; language that has been added is shown underlined and language that has been deleted is shown in brackets.)

1. (Amended) A method of forming a dielectric structure for a flash memory cell, the method comprising:

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01 FC:1202
02 FC:1201
90.00 CH
84.00 CH